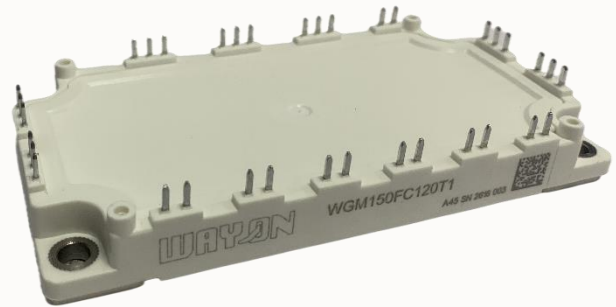


# WGM150FC120T1

1200V, 150A Sixpack IGBT module with Trench Field Stop technology



## Features:

- Trench-FS IGBT
- Low  $V_{CE\ set}$
- Low Switching Loss
- Low  $L_s$
- $T_j\ max=175\ ^\circ C$
- $V_{CE\ set}$  with positive temp. coefficient
- RoHS

## Applications:

- Motor Drives
- Servo Drives

## Maximum Rated Valued of IGBT

集电极-发射极电压 Collector-emitter voltage	$V_{CES}$	$T_J=25^\circ C$	1200	V
栅极-发射极峰值电压 Gate-emitter peak voltage	$V_{GES}$		$\pm 20$	V
连续集电极电流 Continuous collector current	$I_C$	$T_C=100^\circ C$ $T_C=25^\circ C$	150 300	A
集电极重复峰值电流 Repetitive peak collector current	$I_{CM}$	$T_J=175^\circ C, t_P=1ms$	300	A
最大损耗功率 Maximum power dissipation per IGBT	$P_D$	$T_C=25^\circ C$ $T_J\ max=175^\circ C$	1085	W



## Electrical Characteristics of IGBT

			Min.	Typ.	Max.		
集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C=150A, V_{GE}=15V$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$	1.70 1.90 2.00	2.00		V V V
栅极阈值电压 Gate threshold voltage	$V_{GE(th)}$	$I_C=4mA, V_{CE}=V_{GE}$	$T_J=25^\circ C$	5.0	5.7	6.6	V
栅极电荷 Gate charge	$Q_G$	$V_{GE} = -15 V \dots +15 V$	$T_J=25^\circ C$		0.71		$\mu C$
内部栅极电阻 Internal gate resistor	$R_{Gint}$		$T_J=25^\circ C$		5		$\Omega$
输入电容 Input capacitance	$C_{ies}$	$f=1MHz, V_{CE}=25V, V_{GE}=0V$	$T_J=25^\circ C$		10.13		nF
反向传输电容 Reverse transfer capacitance	$C_{res}$	$f=1MHz, V_{CE}=25V, V_{GE}=0V$	$T_J=25^\circ C$		1.01		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$	$T_J=25^\circ C$			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=\pm 20V$	$T_J=25^\circ C$			400	nA
开通延迟时间 (电感负载) Turn-on delay time	$t_{d\ on}$	$V_{CC}=600V, I_C=150A, R_{Gon}=4.7\Omega,$ $V_{GE}=\pm 15V$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		258 258 260		ns ns ns
上升时间 (电感负载) Rise time	$t_r$	$V_{CC}=600V, I_C=150A, R_{Gon}=4.7\Omega,$ $V_{GE}=\pm 15V$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		84 89 89		ns ns ns
关断延迟时间 (电感负载) Turn-off delay time	$t_{d\ off}$	$V_{CC}=600V, I_C=150A, R_{Goff}=4.7\Omega,$ $V_{GE}=\pm 15V$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		263 277 284		ns ns ns
下降时间 (电感负载) Fall time	$t_f$	$V_{CC}=600V, I_C=150A, R_{Goff}=4.7\Omega,$ $V_{GE}=\pm 15V$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		205 376 428		ns ns ns
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	$E_{on}$	$V_{CC}=600V, I_C=150A, R_{Goff}=4.7\Omega,$ $V_{GE}=\pm 15V, di/dt=1550A/\mu s (T_J=150^\circ C)$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		12.5 15.7 17.5		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	$E_{off}$	$V_{CC}=600V, I_C=150A, R_{Goff}=4.7\Omega,$ $V_{GE}=\pm 15V, du/dt=4106V/\mu s (T_J=150^\circ C)$	$T_J=25^\circ C$ $T_J=125^\circ C$ $T_J=150^\circ C$		10.3 15.8 17.4		mJ mJ mJ
短路数据 SC data	$I_{SC}$	$V_{GE}\leq 15V, V_{CC}=600V, R_G=4.7\Omega,$ $t_P\leq 10\mu s$	$T_J=125^\circ C$		680		A
结-外壳热阻 Thermal resistance, junction to case	$R_{th\ JC}$	per leg			0.138		K/W



## Maximum Rated Valued of Diode

反向重复峰值电压 Repetitive peak reverse voltage	$V_{RRM}$		$T_C=25^{\circ}\text{C}$	1200	V
正向连续电流 continuous forward current	$I_F$		$T_C=25^{\circ}\text{C}$	150	A
正向峰值电流 Maximum forward voltage	$I_{FM}$	$t_p=1\text{ms}$	$T_C=25^{\circ}\text{C}$	300	A

## Electrical Characteristics of Diode

			Min.	Typ.	Max.	
正向电压 Forward voltage	$V_F$	$I_F=150\text{A}$	$T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$	1.5 1.5 1.5		V V V
反向恢复峰值电流 Peak reverse recovery current	$I_{RM}$	$V_R=600\text{V}$ , $I_F=150\text{A}$ , $V_{GE}=-15\text{V}$ $-di/dt=1670\text{A}/\mu\text{s}$ ( $T_J=150^{\circ}\text{C}$ )	$T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$	127 142 145		A A A
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_R=600\text{V}$ , $I_F=150\text{A}$ , $V_{GE}=-15\text{V}$ $-di/dt=1670\text{A}/\mu\text{s}$ ( $T_J=150^{\circ}\text{C}$ )	$T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$	371 562 625		ns ns ns
恢复电荷 Recovery charge	$Q_r$	$V_R=600\text{V}$ , $I_F=150\text{A}$ , $V_{GE}=-15\text{V}$ $-di/dt=1670\text{A}/\mu\text{s}$ ( $T_J=150^{\circ}\text{C}$ )	$T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$	22.6 34.6 39.4		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$E_{rec}$	$V_R=600\text{V}$ , $I_F=150\text{A}$ , $V_{GE}=-15\text{V}$ $-di/dt=1670\text{A}/\mu\text{s}$ ( $T_J=150^{\circ}\text{C}$ )	$T_J=25^{\circ}\text{C}$ $T_J=125^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$	9.7 15.2 17.6		mJ mJ mJ
结-外壳热阻 Thermal resistance, junction to case	$R_{thJC}$	per leg		0.212		K/W

## NTC-Thermistor

额定电阻值 Rated resistance	$R_{25}$	$T_C=25^{\circ}\text{C}$	5		K $\Omega$
R100 偏差 Deviation of R100	$\Delta R/R$	$T_C=100^{\circ}\text{C}$ , $R_{100}=481\Omega$		$\pm 5$	%
耗散功率 Power dissipation	$P_{25}$	$T_C=25^{\circ}\text{C}$	50		mW
B-值 B-Value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50} (1/T_2 - 1/(298.15\text{K}))]$	3380		K
B-值 B-Value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80} (1/T_2 - 1/(298.15\text{K}))]$	3440		K



## Module

			Min.	Typ.	Max.	
绝缘电压 Isolation voltage	$V_{ISO}$	f=50Hz, t=1min, RMS, All terminals shorted	2500			V
寄生电感 Stray Inductance Module	$L_s$			19		nH
相对电痕指数 Comparative tracking index	CTI		200			V
最高结温 Maximum junction temperature	$T_{Jmax}$				175	°C
工作结温 Operating junction temperature	$T_{JOP}$		-40		150	°C
储存温度 Storage temperature	$T_{stg}$		-40		125	°C
外壳-散热器热阻 Thermal resistance, case to heatsink	$R_{thCH}$	Thermal grease applied		0.010		K/W
安装扭矩 Mounting torque	T	Mounting screw: M5	3.0		5.0	N·m
重量 Weight	G			300		g



Fig.1 Typical saturation voltage characteristics vs temp.  
IGBT, Inverter

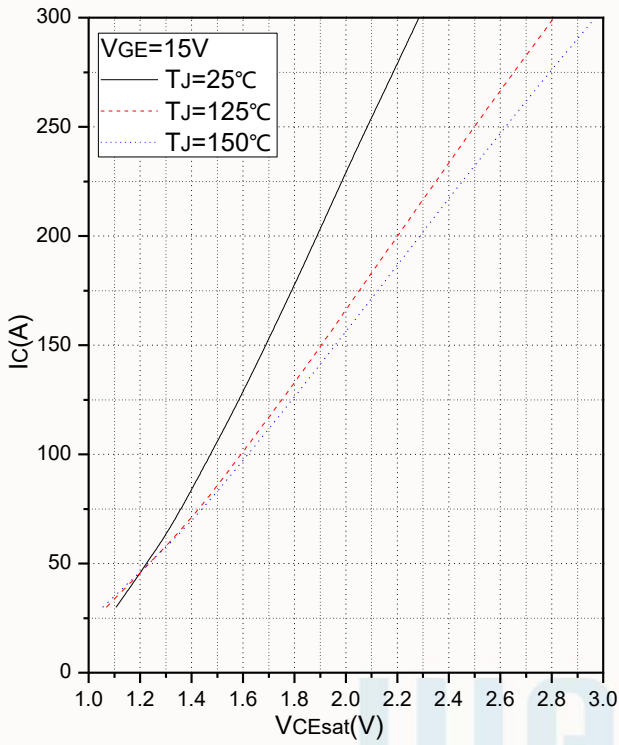


Fig.3 Transfer Characteristic  
IGBT, Inverter

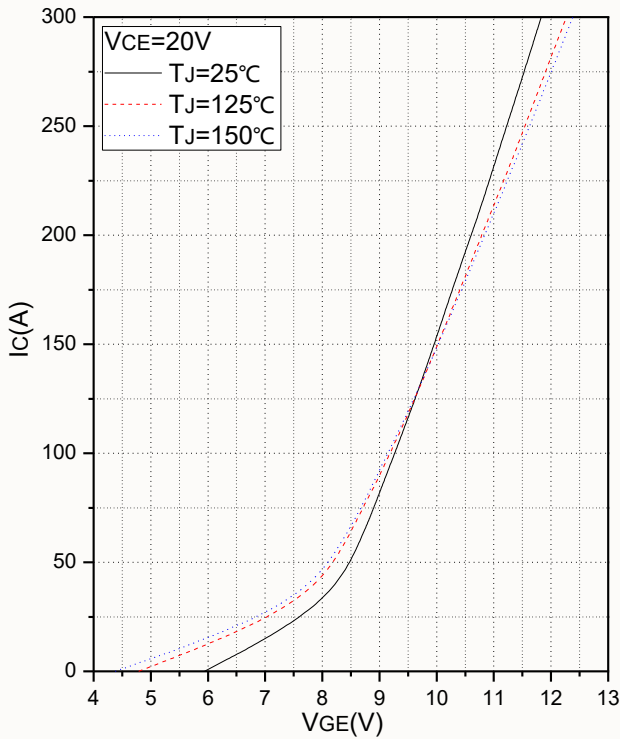


Fig.2 Typical output characteristics vs  $V_{GE}$   
IGBT, Inverter

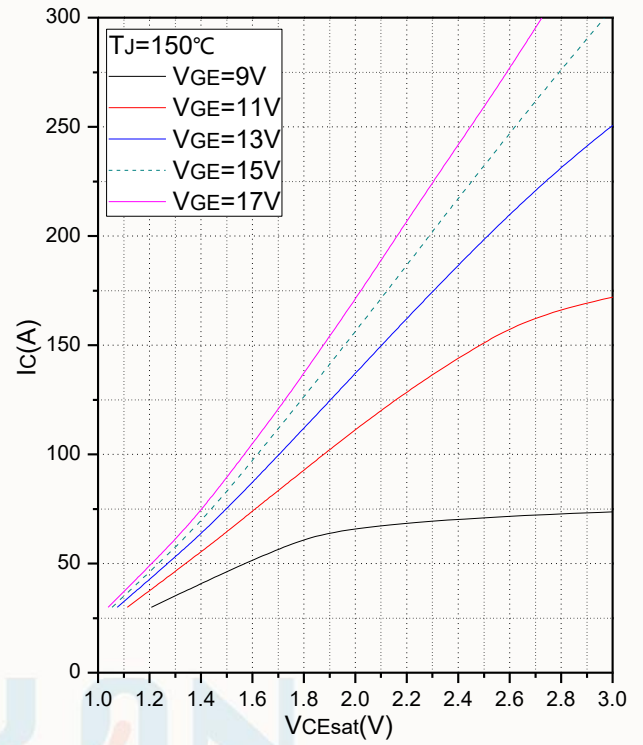


Fig.4 Typical switching loss vs Collector current  
IGBT, Inverter

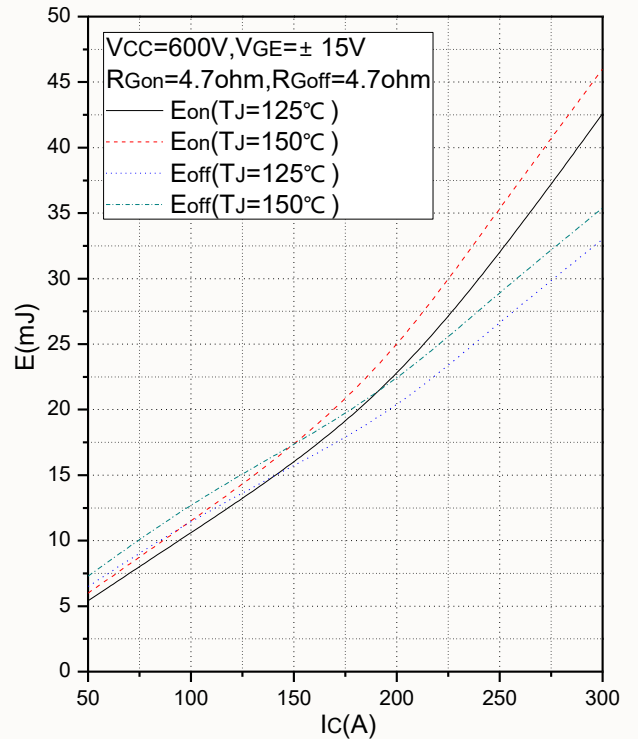


Fig.5 Typical switching loss vs Gate resistance  
IGBT, Inverter

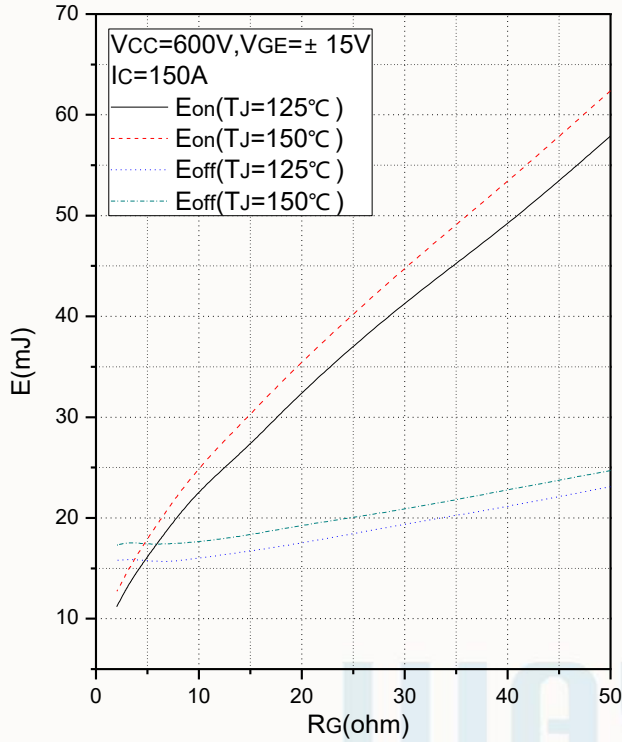


Fig.7 Capacitance Characteristics  
IGBT, Inverter

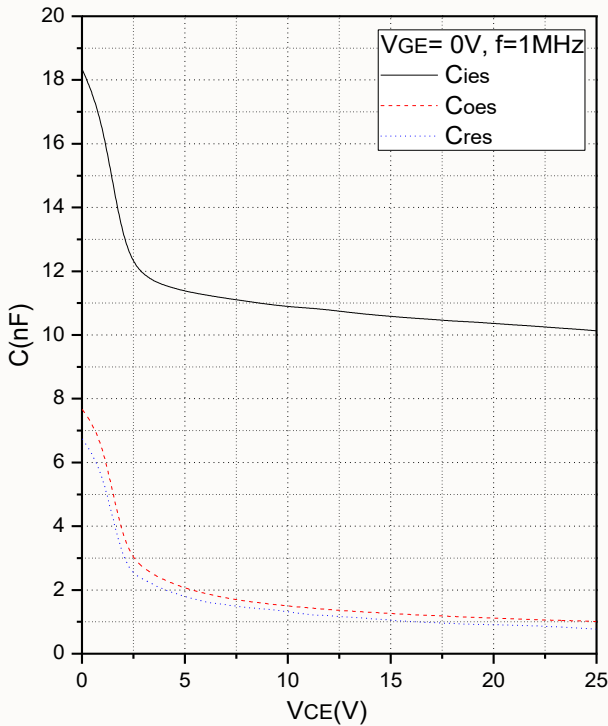


Fig.6 Transient thermal impedance  
IGBT, Inverter

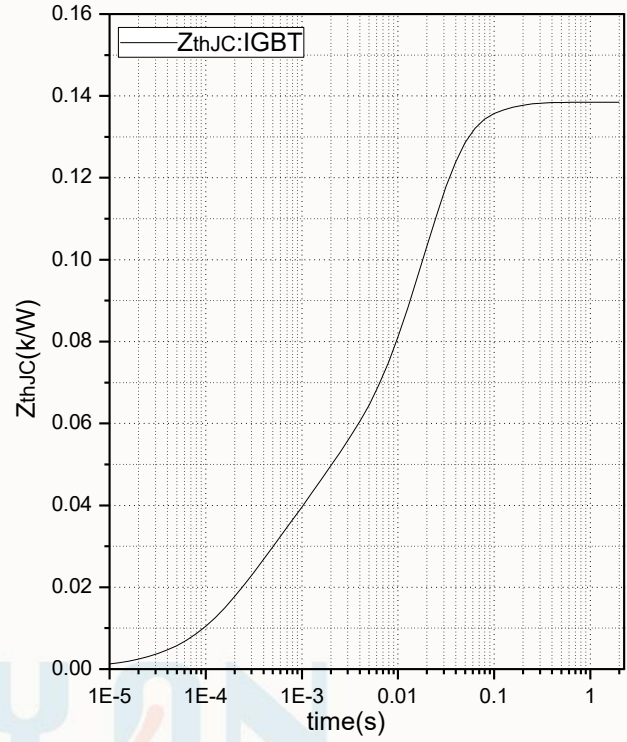


Fig.8 Transient thermal impedance  
IGBT, Inverter

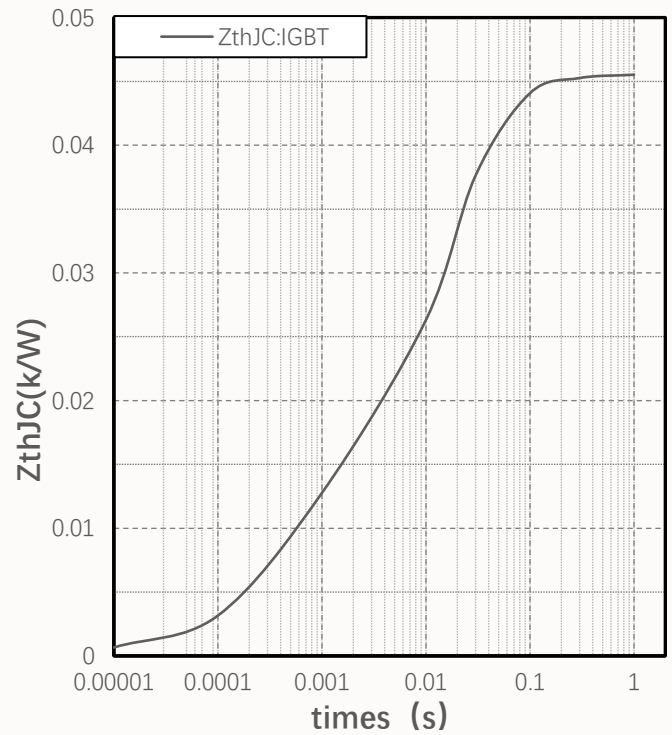


Fig.9 Typical forward characteristic  
Diode, Inverter

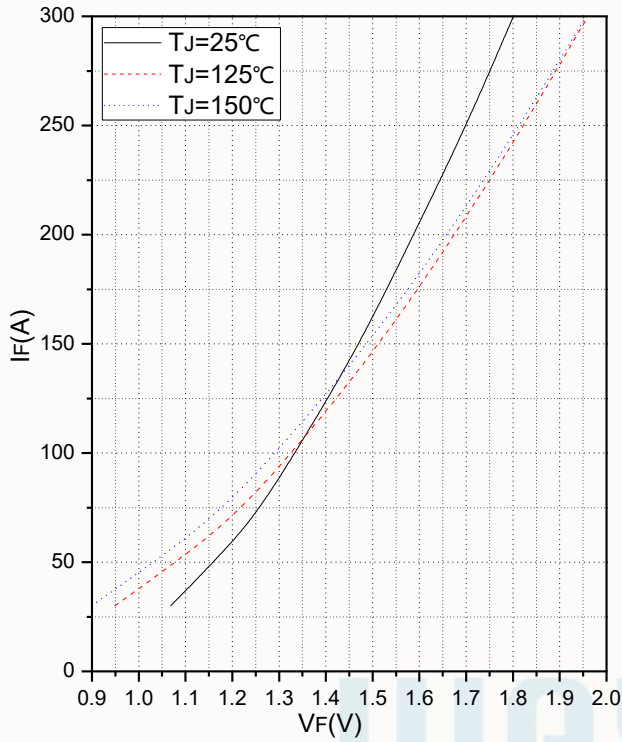


Fig.10 Typical Switching Loss vs. Forward Current  
Diode, Inverter

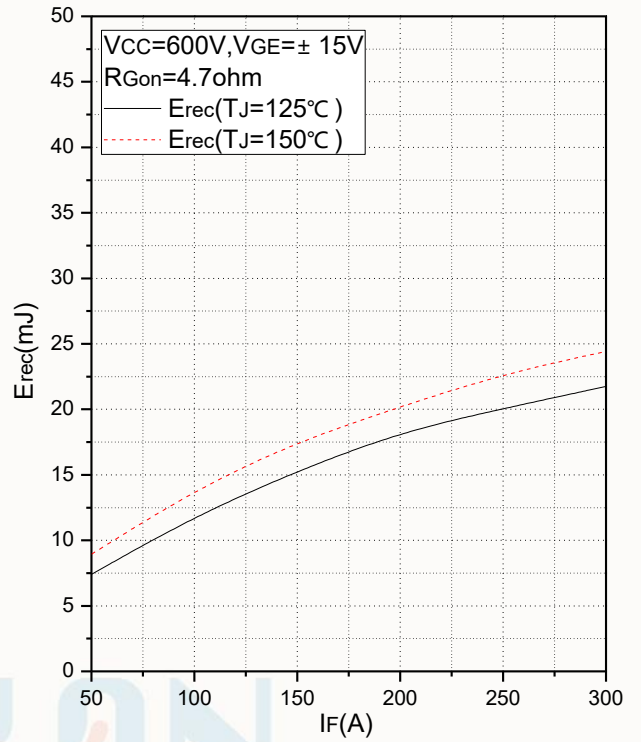


Fig.11 Typical Switching Loss vs. Gate Resistance  
Diode, Inverter

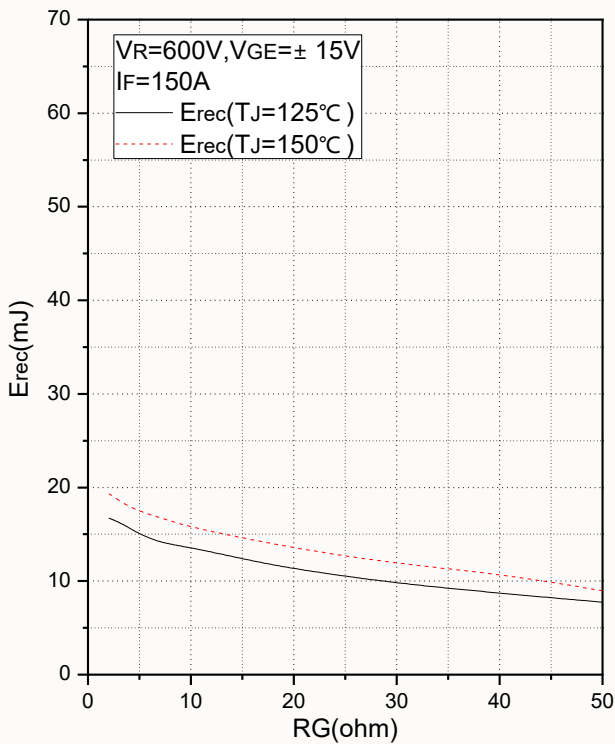


Fig.12 Transient Thermal Impedance  
Diode, Inverter

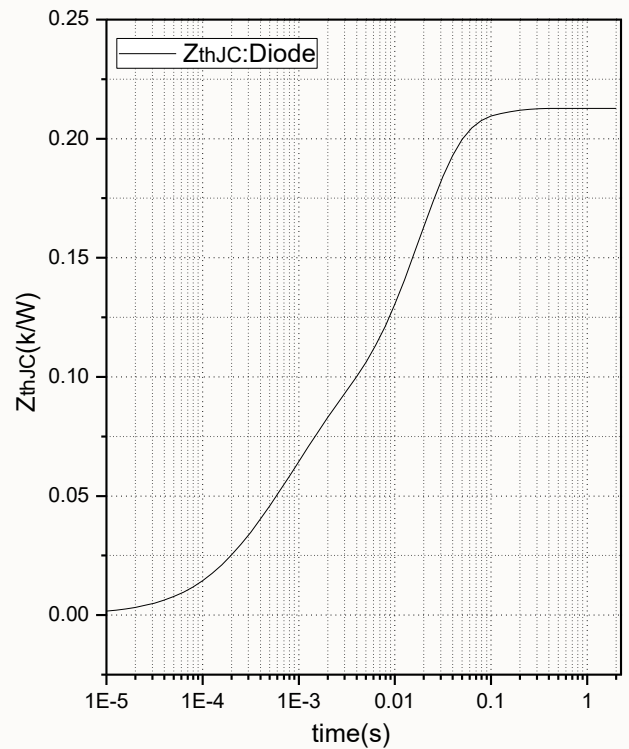




Fig.13 NTC Temperature Characteristics

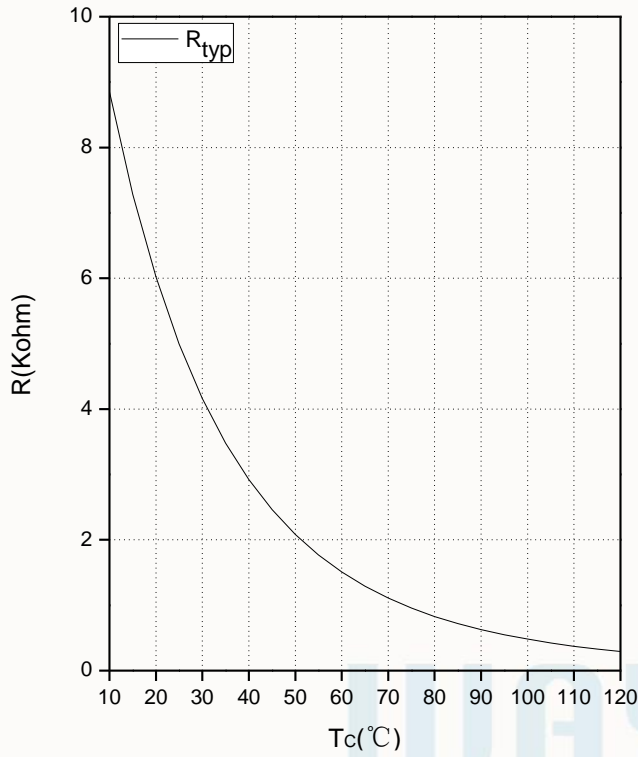
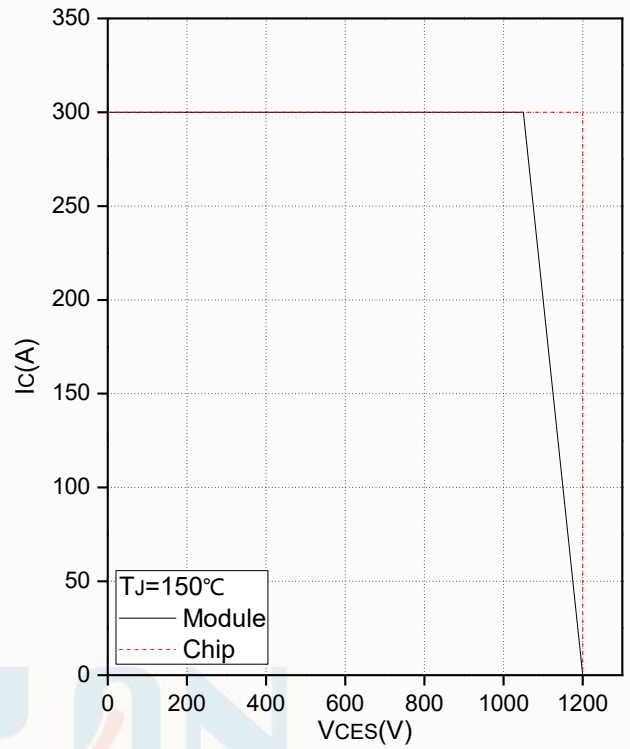
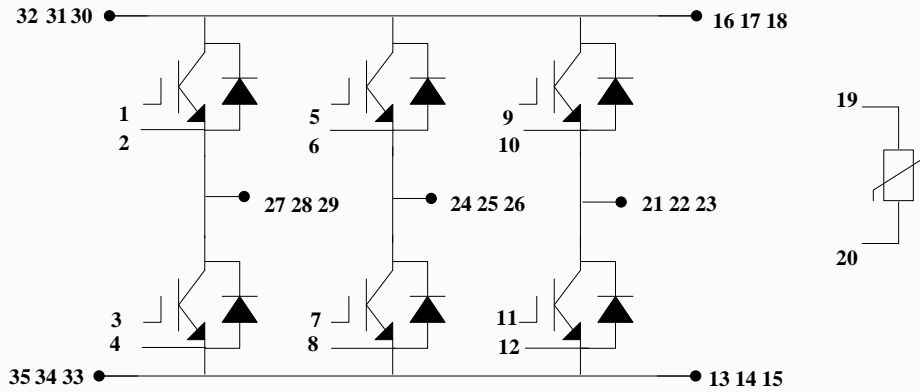


Fig.14 Reverse bias safe operating area (RBSOA) IGBT, Inverter (Tj=150°C)

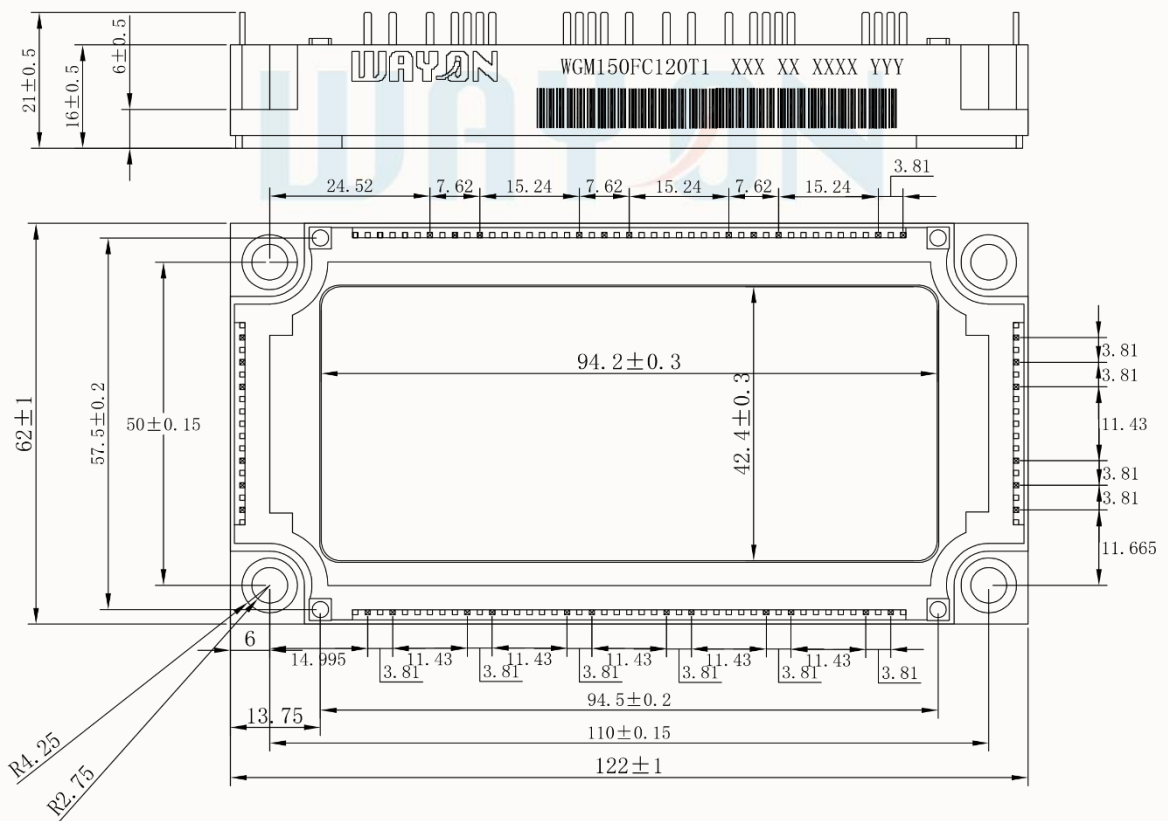




Internal circuit



Package outline (mm)




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